

In the Specification

Delete paragraph [0014] and replace it with the following paragraph:

[0014] The method may include identifying and storing the single frame exposure mask for future use with other EAPSMs in the same mask set as the ~~EAPSM~~~~EAPSM~~, or with other EAPSMs having the same chip or field size as the ~~EAPSM~~~~EAPSM~~.

Delete paragraph [0028] and replace it with the following paragraph:

[0028] In fabricating the EAPSM mask in accordance with the present invention, a second resist layer 28 is applied over the etched opaque and phase shifting image segments created by the first exposure on EAPSM substrate 20, and mask 30 is secured thereover (Fig. 4). Energy source 34, utilizing visible light, UV or other energy beams 36, simultaneously exposes resist layer portion 28a corresponding to the critical area of the mask. After exposure, the second resist layer 28 is developed and exposed area 28 removed, to arrive at the structure shown in Fig. 5. While resist layer portions 28b and 28c remain over the areas outside of the critical structure area, and all resist is removed from within these portions. The remaining opaque layer regions 24a, 24b and ~~25c and 24c~~ within the critical area are then etched away, and the remaining second level resist is removed, which results in the structure shown in Fig. 6. In the finished EAPSM mask depicted, the unwanted opaque layer 24 segments have been removed from within the critical area C, leaving only the chromium layer segments 24d, 24e in the non-critical areas outside of the critical area. The remaining phase shifting image segments 22a, 22b and 22c may now be used in connection with transparent substrate 20 to impart the desired phase shifting pattern, using a photolithographic process, in the active area of integrated circuit device wafer substrate.